## **Supplementary Information**

## PbTe Quantum Dots as Electron Transfer Intermediates for Enhanced Hydrogen Evolution Reaction of Amorphous MoS<sub>x</sub>/TiO<sub>2</sub> Nanotube Arrays

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**Figure S1** XRD patterns of pristine TNAs (a), PbTe/TNAs (b),  $MoS_x/TNAs(c)$  and  $MoS_x@$  PbTe/TNAs (d).



**Figure S2** FE-SEM images of TNAs (a, b), PbTe/TNAs (c, d), MoS<sub>x</sub>/TNAs (e, f) and PbTe@MoS<sub>x</sub>/TNAs (g,h)



Figure S3 EDS elemental mapping images of the PbTe@MoS<sub>x</sub>/TNAs.



**Figure S4** High resolution XPS spectra of (a) Ti2p, (b) Ols, (c) Pb4f and (d) Te3d of the PbTe/TNAs



Figure S5 Raman spectroscopy (a) and PL emission spectra (b) of the samples.

Sample	Te L	Pb M	S K	Mo	O K	Ti K
PbTe/TNAs	1.48	1.02			61.42	36.08
MoS <sub>x</sub> @PbTe/TNAs	6.69	9	4.5	2.56	60.09	17.15

Table S1 Chemical composition of the sample from EDS (at. %)

Sample	Rs (Ω·cm <sup>-</sup> <sup>2</sup> )	$ \begin{array}{c} \mathbf{R}_1  (\mathbf{\Omega} \cdot \mathbf{cm}^2) \end{array} $	$ \begin{array}{c} \mathbf{R}_2  (\mathbf{\Omega} \cdot \mathbf{cm}^2) \end{array} $	C <sub>1</sub> ( <b>F</b> ⋅cm <sup>-</sup> <sup>2</sup> )	C <sub>2</sub> (F·cm <sup>-</sup> <sup>2</sup> )
TNAs	0.5786	6.036	924.2	0.02556	0.009913
PbTe/TNAs	2.541	50.05	183.5	0.0008415	0.01547
MoS <sub>x</sub> /TNAs	1.015	3.340	344.4	0.01453	0.01047
MoS <sub>x</sub> @PbTe/TNA	1.013	3.291	103.8	0.02385	0.01572
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Table S2 Simulated values of the devices in equivalent circuits of the samples